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Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0070			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0100			
I _D (A)	-60			
Configuration	Single			
Package	PowerPAK SO-8L			

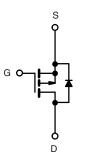
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	-40	V	
Gate-source voltage		V _{GS} ± 20		v	
Continuous drain current	T _C = 25 °C ^a	1	-60		
	T _C = 125 °C	- I _D	-42		
Continuous source current (diode conduction) ^a		I _S	-60	Α	
Pulsed drain current ^b		I _{DM}	-150		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-41		
Single pulse avalanche energy	L = U.T IIII	E _{AS}	84	mJ	
Maximum power dissipation ^b	T _C = 25 °C	D	68	W	
	T _C = 125 °C	P_{D}	22		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	%0	
Soldering recommendations (peak temperature) d, e			260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	68	°C/W
Junction-to-case (drain)		R_{thJC}	2.2	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-2.0	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = -40 V -		-	-1	
	I _{DSS}		V _{DS} = -40 V, T _J = 125 °C	-	-	-50	μΑ
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge -5 \text{ V}$	-30	-	-	Α
Drain-source on-state resistance ^a	, ,	V _{GS} = -10 V	I _D = -10 A	-	0.0058	0.0070	Ω
		V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0106	
	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	-	-	0.0126	
			I _D = -6 A	-	0.0083	0.0100	
Forward transconductance b	9 _{fs}	V _{DS} =	: -15 V, I _D = -10 A	-	54	-	S
Dynamic ^b	1	•					<u> </u>
Input capacitance	C _{iss}		V _{DS} = -25 V, f = 1 MHz	-	8400	11 000	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	620	850	
Reverse transfer capacitance	C _{rss}	7		-	510	700	
Total gate charge c	Q_{g}			-	170	260	
Gate-source charge c	Q _{gs}	V _{GS} = -10 V	$V_{GS} = -10 \text{ V}$ $V_{DS} = -20 \text{ V}, I_{D} = -5 \text{ A}$		24	-	nC
Gate-drain charge ^c	Q _{gd}			-	35	-	
Gate resistance	R _g	f = 1 MHz		0.50	1.08	1.70	Ω
Turn-on delay time c	t _{d(on)}	V_{DD} = -20 V, R_L = 4 Ω I_D \cong -5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	23	35	- ns
Rise time ^c	t _r			-	18	30	
Turn-off delay time c	t _{d(off)}			-	75	120	
Fall time ^c	t _f			-	12	20	
Source-Drain Diode Ratings and Chara	acteristics b	•					<u> </u>
Pulsed current ^a	I _{SM}			-	-	-150	Α
Forward voltage	V _{SD}	I _F = -10 A, V _{GS} = 0 V		-	-0.76	-1.2	V
Body diode reverse recovery time	t _{rr}	l _F = -10 A, dl/dt = 100 A/μs		-	39	90	ns
Body diode reverse recovery charge	Q _{rr}			-	45	100	nC
Reverse recovery fall time	ta			-	22	-	ns
Reverse recovery rise time	t _b			-	19	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.3	-	А

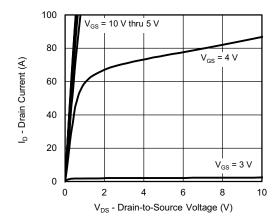
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

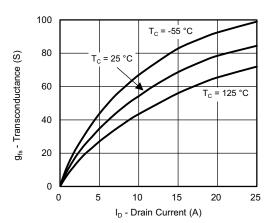
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



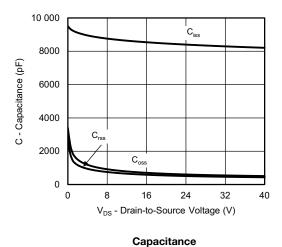
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

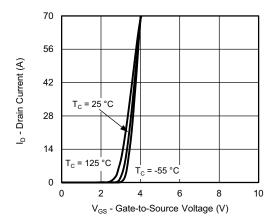


Output Characteristics

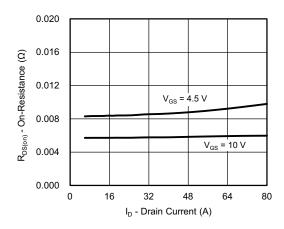


Transconductance

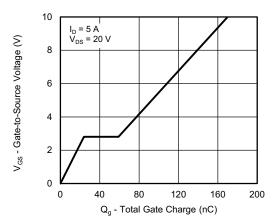




Transfer Characteristics



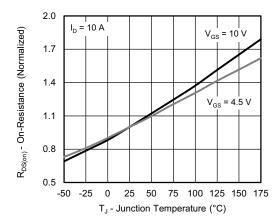
On-Resistance vs. Drain Current



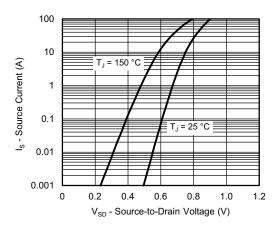
Gate Charge



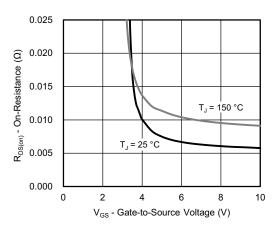
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



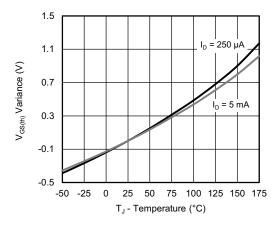
On-Resistance vs. Junction Temperature



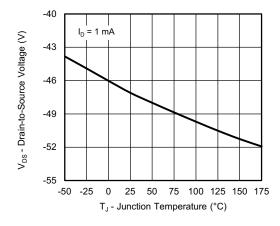
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

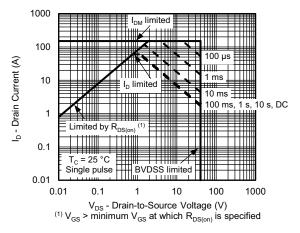


Drain-Source Breakdown vs. Junction Temperature

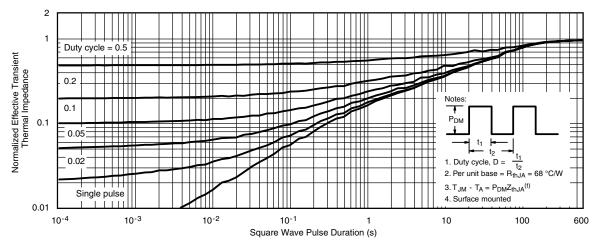
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THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



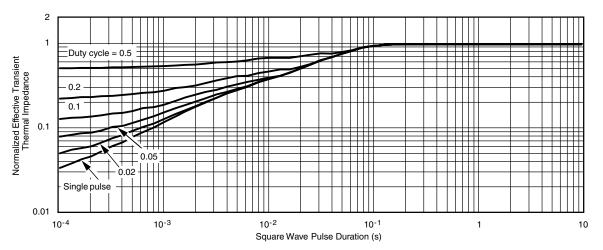
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg277707.



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